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May 2016

# FGA40T65UQDF 650 V, 40 A Field Stop Trench IGBT

### **Features**

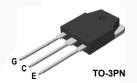
- Maximum Junction Temperature: T<sub>J</sub> = 175°C
- · Positive Temperature Co-efficient for Easy Parallel Operating
- · High Current Capability
- Low Saturation Voltage: V<sub>CE(sat)</sub> = 1.33 V (Typ.) @ I<sub>C</sub> = 40 A
- 100% of the Parts tested for I<sub>LM</sub>(1)
- · High Input Impedance
- · Fast Switching
- · Tighten Parameter Distribution
- · RoHS Compliant

# **General Description**

Using novel field stop IGBT technology, Fairchild's new series of field stop 4th generation IGBTs offer superior conduction and switching performance and easy parallel operation. This device is well suited for the resonant or soft switching application such as induction heating and MWO.

## **Applications**

· Induction Heating, MWO





# **Absolute Maximum Ratings**

Symbol	Description  Collector to Emitter Voltage		FGA40T65UQDF	Unit V	
V <sub>CES</sub>			650		
V <sub>GES</sub>	Gate to Emitter Voltage		± 20	V	
	Transient Gate to Emitter Voltage		± 30	V	
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	80	А	
'C	Collector Current	@ T <sub>C</sub> = 100°C	40	А	
I <sub>LM</sub> (1)	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	120	А	
I <sub>CM</sub> (2)	Pulsed Collector Current		120	Α	
I <sub>F</sub>	Diode Forward Current	@ T <sub>C</sub> = 25°C	40	А	
	Diode Forward Current	20	А		
I <sub>FM</sub>	Pulsed Diode Maximum Forward Current		60	А	
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	231	W	
' Б	Maximum Power Dissipation @ $T_C = 100^{\circ}C$		115	W	
T <sub>J</sub>	Operating Junction Temperature		-55 to +175	°C	
T <sub>stg</sub>	Storage Temperature Range		-55 to +175	°C	
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 second	300	°C		

- 1.  $\rm V_{CC}$  = 400 V,  $\rm V_{GE}$  = 15 V,  $\rm I_C$  = 120 A,  $\rm R_G$  = 20  $\Omega$ , Inductive Load 2. Repetitive rating: Pulse width limited by max. junction temperature

# **Thermal Characteristics**

Symbol	Parameter	FGA40T65UQDF	Unit
R <sub>θJC</sub> (IGBT)	Thermal Resistance, Junction to Case, Max.	0.65	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance, Junction to Case, Max.	1.75	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	°C/W

# **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Qty per Tube	
FGA40T65UQDF	FGA40T65UQDF	TO-3PN	-	-	30	

# Electrical Characteristics of the IGBT $T_C = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 1 mA	650	-	-	V
ΔBV <sub>CES</sub> / ΔΤ <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 1 mA	-	0.52	-	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0 V	-	ç -	250	μА
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	± 400	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	I <sub>C</sub> = 40 mA, V <sub>CE</sub> = V <sub>GE</sub>	2.5	4.0	5.5	V
()		I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V	-	1.33	1.67	V
V <sub>CE(sat)</sub> Collector to Emitter Saturation Voltage		I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 175°C	-	1.5	-	V
Dynamic C	haracteristics		1			
C <sub>ies</sub>	Input Capacitance		_	7309	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$	-	58	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz	-	30	-	pF
Switching	Characteristics					
T <sub>d(on)</sub>	Turn-On Delay Time		<i>A</i> -	32	- //	ns
T <sub>r</sub>	Rise Time		-	18	-	ns
T <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 40 \text{ A},$	-	271	/-	ns
T <sub>f</sub>	Fall Time	$R_G = 6 \Omega$ , $V_{GF} = 15 V$ ,	-	11		ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C	-	989	- //	μJ
E <sub>off</sub>	Turn-Off Switching Loss		-	310	- 1	μJ
E <sub>ts</sub>	Total Switching Loss		-	1299	- \	μJ
T <sub>d(on)</sub>	Turn-On Delay Time		-	30	-	ns
T <sub>r</sub>	Rise Time		-	22	-	ns
T <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC}$ = 400 V, $I_{C}$ = 40 A, $R_{G}$ = 6 $\Omega$ , $V_{GE}$ = 15 V, Inductive Load, $T_{C}$ = 175°C	-	298	-	ns
T <sub>f</sub>	Fall Time		-	16	-	ns
E <sub>on</sub>	Turn-On Switching Loss		-	1400	-	μJ
E <sub>off</sub>	Turn-Off Switching Loss		-	553	-	μJ
E <sub>ts</sub>	Total Switching Loss		-	1953	-	μJ

# **Electrical Characteristics of the IGBT** (Continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Qg	Total Gate Charge		-	306	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	V <sub>CE</sub> = 400 V, I <sub>C</sub> = 40 A, V <sub>GF</sub> = 15 V	-	30	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	VGE - 10 V	-	77	-	nC

# Electrical Characteristics of the Diode T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter		Test Condition	ns	Min.	Тур.	Max.	Unit
V <sub>FM</sub>	Diode Forward Voltage	l- =	20 A	T <sub>C</sub> = 25°C	-	1.5	1.95	V
FIM	2.000 : 0.11010 : 0.100g0	'F =		T <sub>C</sub> = 175°C	-	1.39	-	
E <sub>rec</sub>	Reverse Recovery Energy			T <sub>C</sub> = 175°C	-	115	-	μJ
Т	Diode Reverse Recovery Time	  =	20 A, dI <sub>F</sub> /dt = 200 A/μs	T <sub>C</sub> = 25°C	-	89	-	ns
l ru	Blode Reverse Recovery Time	ip = 20 A, dip/di	20 A, αιτ/αι - 200 A/μS	T <sub>C</sub> = 175°C	/ -	251	-	]
Q <sub>rr</sub>	Diode Reverse Recovery Charge			T <sub>C</sub> = 25°C	-	289	-	nC
GIT .	Diodo Novoloo Nocovery Charge			T <sub>C</sub> = 175°C	-	1502	-	]

**Figure 1. Typical Output Characteristics** 

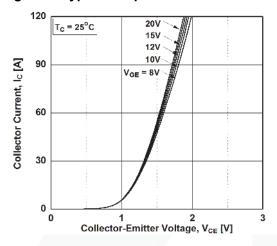


Figure 3. Typical Saturation Voltage Characteristics

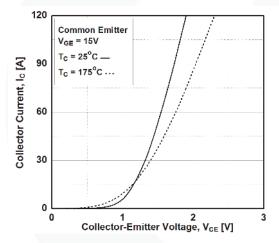
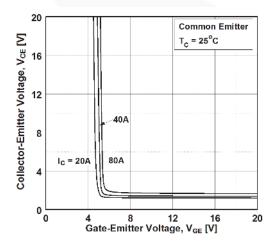


Figure 5. Saturation Voltage vs. V<sub>GE</sub>



**Figure 2. Typical Output Characteristics** 

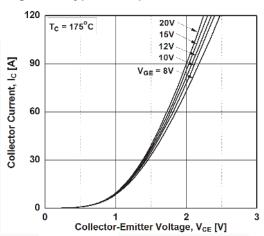


Figure 4. Saturation Voltage vs. Case
Temperature at Variant Current Level

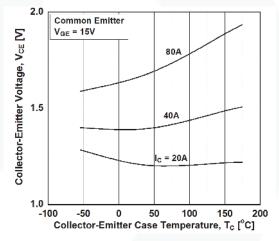


Figure 6. Saturation Voltage vs.  $V_{GE}$ 

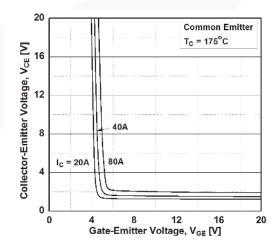


Figure 7. Capacitance Characteristics

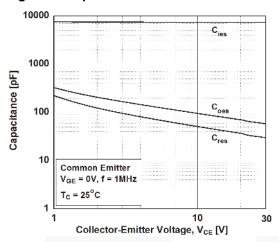


Figure 8. Gate charge Characteristics

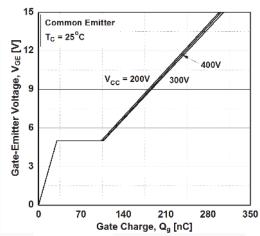


Figure 9. Turn-on Characteristics vs.
Gate Resistance

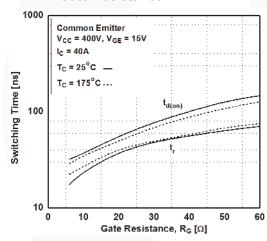


Figure 10. Turn-off Characteristics vs. Gate Resistance

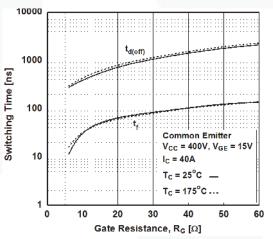


Figure 11. Switching Loss vs.
Gate Resistance

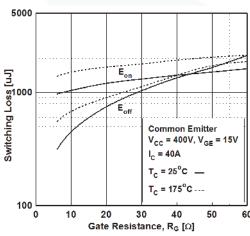


Figure 12. Turn-on Characteristics vs. Collector Current

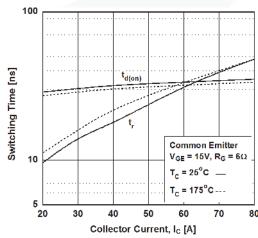


Figure 13. Turn-off Characteristics vs. Collector Current

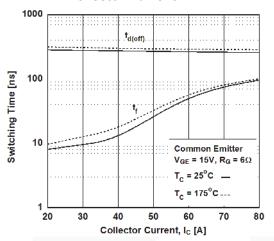


Figure 14. Switching Loss vs. Collector Current

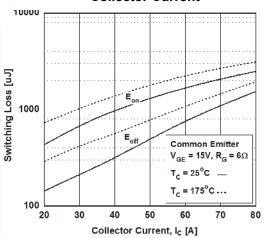


Figure 15. Load Current Vs. Frequency

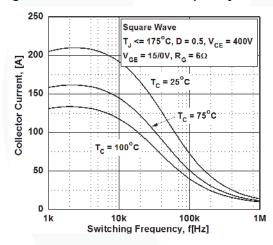


Figure 16. SOA Characteristics

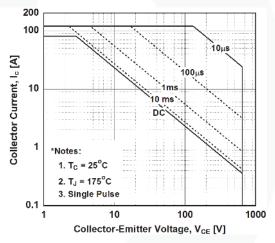


Figure 17. Forward Characteristics

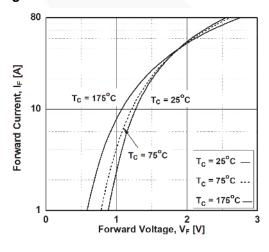


Figure 18. Reverse Recovery Current

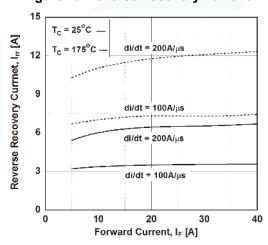


Figure 19. Reverse Recovery Time

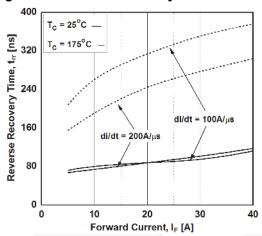


Figure 20. Stored Charge

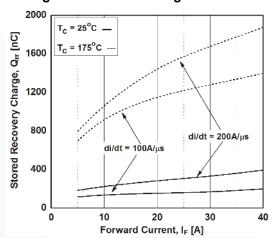


Figure 21. Transient Thermal Impedance of IGBT

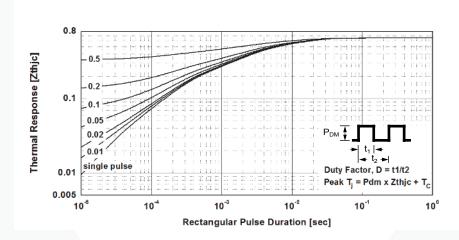
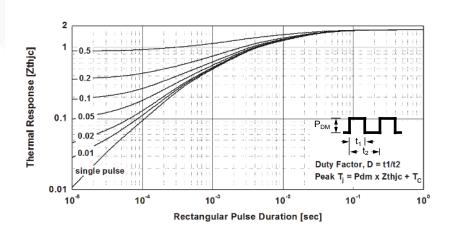


Figure 22. Transient Thermal Impedance of Diode



### **Mechanical Dimensions**

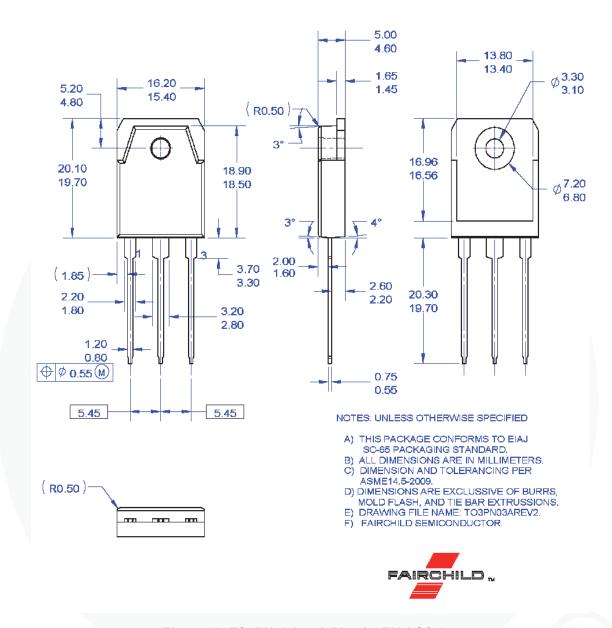


Figure 23. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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